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SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR
(AUTONOMOUS)

B.Tech IV Year I Semester Supplementary Examinations August-2021

VLSI DESIGN

(Electronics and Communication Engineering)

Time: 3 hours

Max. Marks: 60

(Answer all Five Units 5 x 12 = 60 Marks)

UNIT-I

- 1 a Explain the steps involved in the fabrication of a n-well process CMOS transistor. 6M
b Compare CMOS with BJT in different aspects. 6M

OR

- 2 a Explain the operation of BICMOS inverter with neat diagram. 6M
b Discuss about (i) Threshold Voltage V_t (ii) Trans-conductance g_m 6M
(iii) Output conductance g_{ds} .

UNIT-II

- 3 a Explain the VLSI design flow. 8M
b Design the stick diagram for CMOS Inverter. 4M

OR

- 4 a Explain how PMOS transistor designed using lambda-based design rule. 7M
b Create the stick diagram for (AB+CD) using NMOS design style. 5M

UNIT-III

- 5 a Design CMOS implementation of 2x1 MUX using transmission gates. 6M
b Discuss NORA Logic. 6M

OR

- 6 a Explain AOI implementation using CMOS design style. 5M
b Explain clock and power distribution in VLSI Design circuits with neat diagrams. 7M

UNIT-IV

- 7 a Construct 4*4 array multiplier. 6M
b Design and Explain 3 bit LFSR with example. 6M

OR

- 8 a Explain the 6 transistor static memory cell. 6M
b Design and Explain ripple counter. 6M

UNIT-V

- 9 a Explain the architecture of FPGA. 6M
b What is the need for testing? Explain about Fault simulation. 6M

OR

- 10 a Design the PAL Structure for the Boolean function $Y = AB'C' + ABC + A'B'C' + A'BC$. 6M
b Explain stuck at 1 and stuck at 0 faults with neat diagram. 6M

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